

# Maksim G Kozodaev

## List of Publications by Year in descending order

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31  
papers

1,197  
citations

516710

16  
h-index

414414

32  
g-index

32  
all docs

32  
docs citations

32  
times ranked

1061  
citing authors

#	ARTICLE	IF	CITATIONS
1	Microextrusion printing of gas-sensitive planar anisotropic NiO nanostructures and their surface modification in an H <sub>2</sub> S atmosphere. Applied Surface Science, 2022, 578, 151984.	6.1	23
2	Origin of the retention loss in ferroelectric Hf <sub>0.5</sub> Zr <sub>0.5</sub> O <sub>2</sub> -based memory devices. Acta Materialia, 2021, 204, 116515.	7.9	36
3	Band Alignment of Graphene/MoS <sub>2</sub> /Fluorine Tin Oxide Heterojunction for Photodetector Application. Physica Status Solidi (A) Applications and Materials Science, 2021, 218, 2000744.	1.8	1
4	Electroresistance effect in MoS <sub>2</sub> -Hf <sub>0.5</sub> Zr <sub>0.5</sub> O <sub>2</sub> heterojunctions. Applied Physics Letters, 2021, 118, .	3.3	13
5	Microplotter printing of planar solid electrolytes in the CeO <sub>2</sub> -Y <sub>2</sub> O <sub>3</sub> system. Journal of Colloid and Interface Science, 2021, 588, 209-220.	9.4	28
6	Interface engineering for enhancement of the analog properties of W/WO <sub>3</sub> /HfO <sub>2</sub> /Pd resistance switched structures. Journal Physics D: Applied Physics, 2021, 54, 504004.	2.8	8
7	Thickness-Dependent Structural and Electrical Properties of WS <sub>2</sub> Nanosheets Obtained via the ALD-Grown WO <sub>3</sub> Sulfurization Technique as a Channel Material for Field-Effect Transistors. ACS Omega, 2021, 6, 34429-34437.	3.5	16
8	Forming-Free Nonfilamentary Resistive Switching in W/WO <sub>3</sub> /HfO <sub>2</sub> /Pd Structures. Nanobiotechnology Reports, 2021, 16, 737-744.	0.6	3
9	Band Alignment in As-Transferred and Annealed Graphene/MoS <sub>2</sub> Heterostructures. Physica Status Solidi - Rapid Research Letters, 2020, 14, 1900406.	2.4	14
10	Influence of ALD Ru bottom electrode on ferroelectric properties of Hf <sub>0.5</sub> Zr <sub>0.5</sub> O <sub>2</sub> -based capacitors. Applied Physics Letters, 2020, 117, .	3.3	15
11	Radical-Enhanced Atomic Layer Deposition of a Tungsten Oxide Film with the Tunable Oxygen Vacancy Concentration. Journal of Physical Chemistry C, 2020, 124, 18156-18164.	3.1	14
12	Influence of Reducing Agent on Properties of Thin WS <sub>2</sub> Nanosheets Prepared by Sulfurization of Atomic Layer-Deposited WO <sub>3</sub> . Journal of Physical Chemistry C, 2020, 124, 28169-28177.	3.1	9
13	Resistance Switching Peculiarities in Nonfilamentary Self-Rectified TiN/Ta <sub>2</sub> O <sub>5</sub> /Ta and TiN/HfO <sub>2</sub> /Ta <sub>2</sub> O <sub>5</sub> /Ta Stacks. Physica Status Solidi (A) Applications and Materials Science, 2020, 217, 1900952.	1.8	18
14	Pen plotter printing of Co <sub>3</sub> O <sub>4</sub> thin films: features of the microstructure, optical, electrophysical and gas-sensing properties. Journal of Alloys and Compounds, 2020, 832, 154957.	5.5	38
15	Ferroelectric Second-Order Memristor. ACS Applied Materials & Interfaces, 2019, 11, 32108-32114.	8.0	77
16	Synthesis of Large Area Two-Dimensional MoS <sub>2</sub> Films by Sulfurization of Atomic Layer Deposited MoO <sub>3</sub> Thin Film for Nanoelectronic Applications. ACS Applied Nano Materials, 2019, 2, 7521-7531.	5.0	34
17	Temperature controlled Ru and RuO <sub>2</sub> growth via O* radical-enhanced atomic layer deposition with Ru(EtCp) <sub>2</sub> . Journal of Chemical Physics, 2019, 151, 204701.	3.0	18
18	Mitigating wakeup effect and improving endurance of ferroelectric HfO <sub>2</sub> -ZrO <sub>2</sub> thin films by careful La-doping. Journal of Applied Physics, 2019, 125, .	2.5	110

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19	Size-ordered 63Ni nanocluster film as a betavoltaic battery unit. Applied Physics Letters, 2018, 112, .	3.3	5
20	Improved Ferroelectric Switching Endurance of La-Doped Hf <sub>0.5</sub> Zr <sub>0.5</sub> O <sub>2</sub> Thin Films. ACS Applied Materials & Interfaces, 2018, 10, 2701-2708.	8.0	207
21	La-doped Hf <sub>0.5</sub> Zr <sub>0.5</sub> O <sub>2</sub> thin films for high-efficiency electrostatic supercapacitors. Applied Physics Letters, 2018, 113, .	3.3	43
22	Leakage Currents Mechanism in Thin Films of Ferroelectric Hf <sub>0.5</sub> Zr <sub>0.5</sub> O <sub>2</sub> . ECS Transactions, 2017, 75, 123-129.	0.5	13
23	Low temperature plasma-enhanced ALD TiN ultrathin films for Hf <sub>0.5</sub> Zr <sub>0.5</sub> O <sub>2</sub> -based ferroelectric MIM structures. Physica Status Solidi (A) Applications and Materials Science, 2017, 214, 1700056.	1.8	20
24	Ferroelectric properties of lightly doped La:HfO <sub>2</sub> thin films grown by plasma-assisted atomic layer deposition. Applied Physics Letters, 2017, 111, .	3.3	69
25	Leakage currents mechanism in thin films of ferroelectric Hf <sub>0.5</sub> Zr <sub>0.5</sub> O <sub>2</sub> . Journal of Physics: Conference Series, 2017, 864, 012002.	0.4	4
26	Ferroelectric properties of full plasma-enhanced ALD TiN/La:HfO <sub>2</sub> /TiN stacks. Applied Physics Letters, 2016, 108, .	3.3	79
27	Charge transport in thin layers of ferroelectric Hf <sub>0.5</sub> Zr <sub>0.5</sub> O <sub>2</sub> . Russian Microelectronics, 2016, 45, 350-356.	0.5	1
28	Ultrathin Hf <sub>0.5</sub> Zr <sub>0.5</sub> O <sub>2</sub> Ferroelectric Films on Si. ACS Applied Materials & Interfaces, 2016, 8, 7232-7237.	8.0	186
29	Charge transport mechanism in thin films of amorphous and ferroelectric Hf <sub>0.5</sub> Zr <sub>0.5</sub> O <sub>2</sub> . JETP Letters, 2015, 102, 544-547.	1.4	25
30	Structural, chemical and electrical properties of ALD-grown Hf <sub>x</sub> Al <sub>1-x</sub> O <sub>y</sub> thin films for MIM capacitors. Physica Status Solidi (B): Basic Research, 2015, 252, 701-708.	1.5	4
31	Confinement-free annealing induced ferroelectricity in Hf <sub>0.5</sub> Zr <sub>0.5</sub> O <sub>2</sub> thin films. Microelectronic Engineering, 2015, 147, 15-18.	2.4	64